Supplementary Information

MOCVD-grown Ga_2O_3 as a gate dielectric on AlGaN/GaN based heterojunction field effect transistor.

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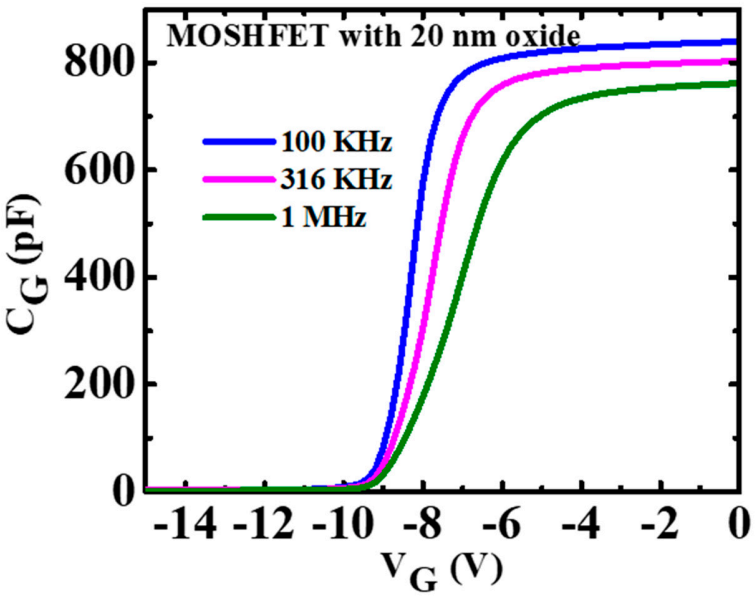
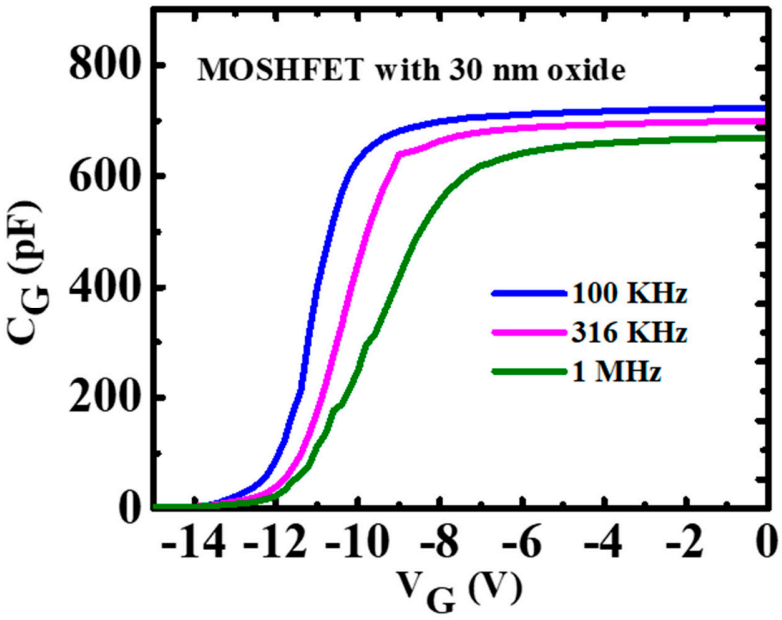
(a)



(b)



(c)

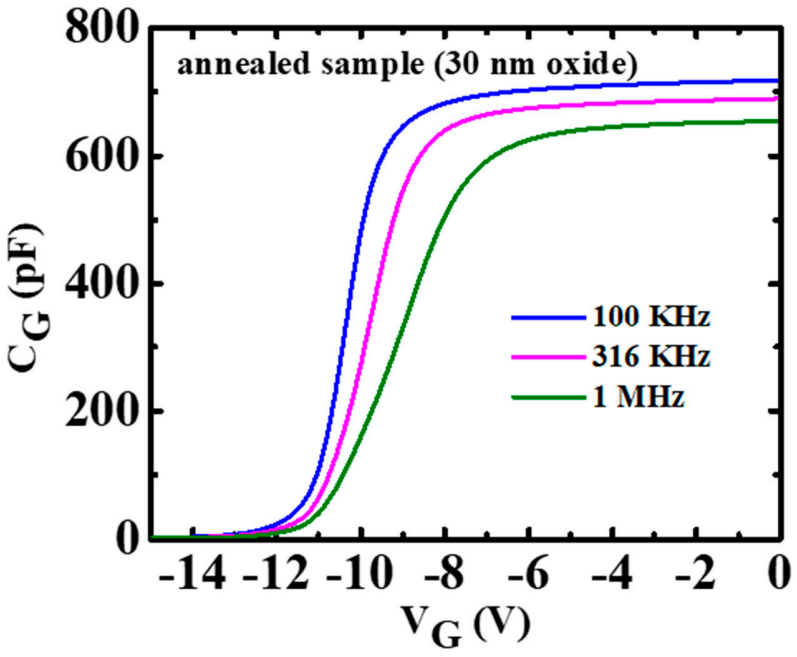


Figure S1. Frequency-dependent CV measurements of M□SHFET with (a) 20 nm thick gate oxide (b) 30 nm thick gate oxide, and (c) annealed 30 nm thick gate oxide.

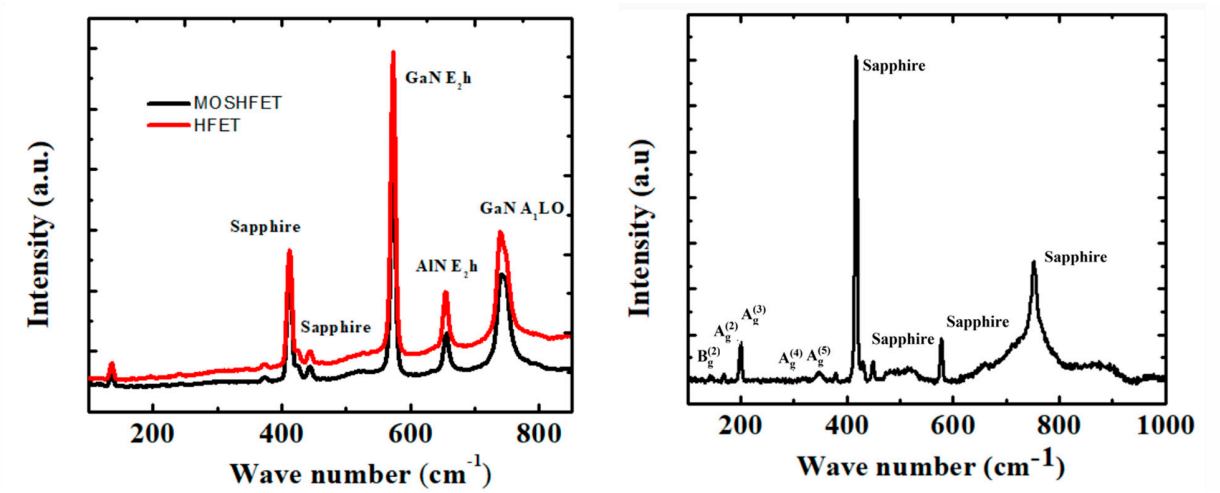


Figure S2. (a) Raman spectra of HFET and M□SHFET (30 nm oxide), (b) Raman spectra of Ga_2□$_3$ on sapphire to identify the Ga2□3 signature peak positions.